

Silicon PNP Power Transistors

2SB1481

DESCRIPTION

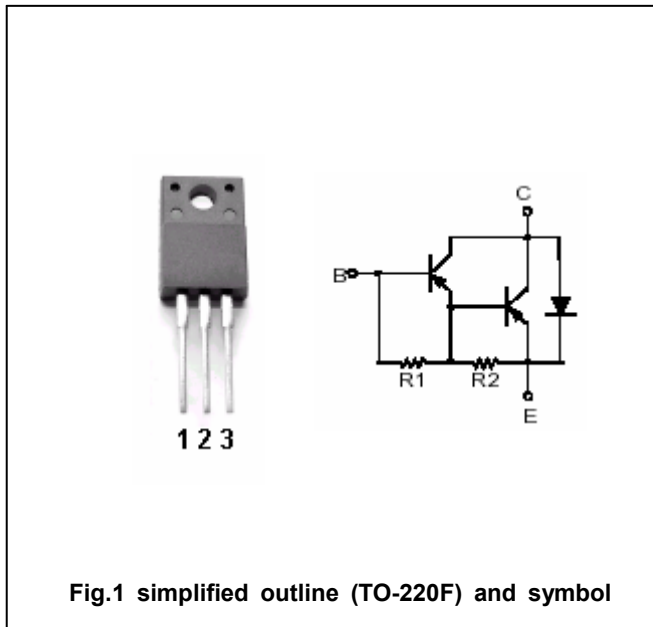
- With TO-220F package
- Complement to type 2SD2241
- High DC current gain.
- Low saturation voltage.
- DARLINGTON

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		±4	A
I _{CM}	Collector current-peak		±6	A
P _C	Collector dissipation	T _C =25°C	25	W
		T _a =25°C	2	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-6mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3A; I _B =-6mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-2	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-2.5	mA
h _{FE-1}	DC current gain	I _C =-1.5A; V _{CE} =-2V	2000			
h _{FE-2}	DC current gain	I _C =-3A; V _{CE} =-2V	1000			
V _{ECO}	Diode forward voltage	I _C =1A; I _B =0			2.0	V

t _{on}	Turn-on time	I _{B1} =-I _{B2} =-6mA V _{CC} =-30V; R _L =10Ω		0.15		μs
t _{stg}	Storage time			0.80		μs
t _f	Fall time			0.40		μs

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PACKAGE OUTLINE

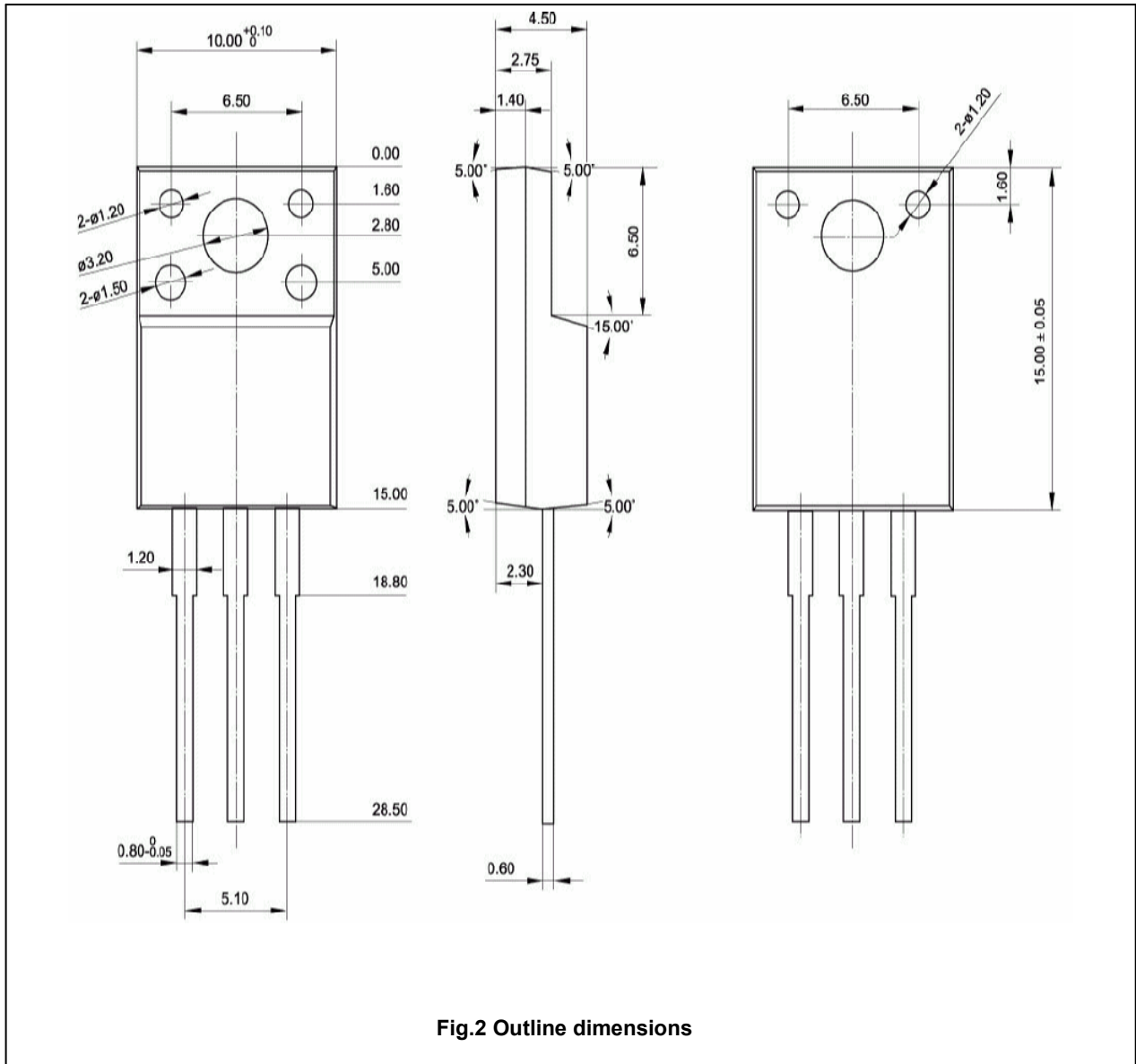


Fig.2 Outline dimensions